David J Smith

List of Publications by Year
in descending order

675 papers	21,816 citations	10956 71 h-index	22764 112 g-index
685 all docs	685 docs citations	685 times ranked	17931 citing authors

#	Article	IF	Citations
1	Bulk Production of a New Form of sp² Carbon: Crystalline Graphene Nanoribbons. Nano Letters, 2008, 8, 2773-2778.	4.5	588
2	Giant magnetoresistance in antiferromagnetic Co/Cu multilayers. Applied Physics Letters, 1991, 58, 2710-2712.	1.5	582
3	Ex-MWNTs: Graphene Sheets and Ribbons Produced by Lithium Intercalation and Exfoliation of Carbon Nanotubes. Nano Letters, 2009, 9, 1527-1533.	4.5	369
4	Urine Steroid Metabolomics as a Biomarker Tool for Detecting Malignancy in Adrenal Tumors. Journal of Clinical Endocrinology and Metabolism, 2011, 96, 3775-3784.	1.8	369
5	Covalently bonded three-dimensional carbon nanotube solids via boron induced nanojunctions. Scientific Reports, 2012, 2, 363.	1.6	329
6	An investigation of grain boundaries in submicrometer-grained Al-Mg solid solution alloys using high-resolution electron microscopy. Journal of Materials Research, 1996, 11, 1880-1890.	1.2	317
7	Direct surface imaging in small metal particles. Nature, 1983, 303, 316-317.	13.7	250
8	Human spermatozoa migration in microchannels reveals boundary-following navigation. Proceedings of the National Academy of Sciences of the United States of America, 2012, 109, 8007-8010.	3.3	247
9	Geâ€“Sn semiconductors for band-gap and lattice engineering. Applied Physics Letters, 2002, 81, 2992-2994.	1.5	237
10	Observation of ferromagnetism above 900K in Crâ€“GaN and Crâ€“AlN. Applied Physics Letters, 2004, 85, 4076-4078.	1.5	207
11	Nitrogen-Mediated Carbon Nanotube Growth: Diameter Reduction, Metallicity, Bundle Dispersability, and Bamboo-like Structure Formation. ACS Nano, 2007, 1, 369-375.	7.3	207
12	Heterodoped Nanotubes: Theory, Synthesis, and Characterization of Phosphorusâˆ’Nitrogen Doped Multiwalled Carbon Nanotubes. ACS Nano, 2008, 2, 441-448.	7.3	192
13	High resolution studies of small particles of gold and silver. Journal of Crystal Growth, 1981, 54, 425-432.	0.7	178
14	Thermal refugia against coral bleaching throughout the northern Red Sea. Global Change Biology, 2018, 24, e474-e484.	4.2	177
15	Atomic Structure of Symmetric Tilt Grain Boundaries in NiO. Physical Review Letters, 1987, 59, 2887-2890.	2.9	176
16	The importance of beam alignment and crystal tilt in high resolution electron microscopy. Ultramicroscopy, 1983, 11, 263-281.	0.8	173
17	Strain-Driven Alloying in Ge/Si(100) Coherent Islands. Physical Review Letters, 1999, 83, 1199-1202.	2.9	171
18	Imaging of atomic clouds outside the surfaces of gold crystals by electron microscopy. Nature, 1985, 317, 47-49.	13.7	170

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19	Electron Holography: Phase Imaging with Nanometer Resolution. Annual Review of Materials Research, 2007, 37, 729-767.	4.3	170
20	Synthesis, characterization, and modeling of high quality ferromagnetic Cr-doped AlN thin films. Applied Physics Letters, 2003, 82, 3047-3049.	1.5	166
21	Accurate measurements of mean inner potential of crystal wedges using digital electron holograms. Ultramicroscopy, 1993, 50, 285-299.	0.8	158
22	Formation of threading defects in GaN wurtzite films grown on nonisomorphic substrates. Applied Physics Letters, 1995, 67, 2063-2065.	1.5	158
23	Observations of grain boundary structure in submicrometer-grained Cu and Ni using high-resolution electron microscopy. Journal of Materials Research, 1998, 13, 446-450.	1.2	150
24	Evolution of Ge/Si(100) islands: Island size and temperature dependence. Journal of Applied Physics, 2000, 87, 2245-2254.	1.1	148
25	Efficient Anchoring of Silver Nanoparticles on N-Doped Carbon Nanotubes. Small, 2006, 2, 346-350.	5.2	143
26	Ultimate resolution in the electron microscope?. Materials Today, 2008, 11, 30-38.	8.3	140
27	Above 400-K robust perpendicular ferromagnetic phase in a topological insulator. Science Advances, 2017, 3, e1700307.	4.7	138
28	The Study of Heterogeneous Catalysts by High-Resolution Transmission Electron MicroscoDV. Catalysis Reviews - Science and Engineering, 1992, 34, 129-178.	5.7	136
29	Deep ultraviolet emitting AlGaN quantum wells with high internal quantum efficiency. Applied Physics Letters, 2009, 94, .	1.5	130
30	Direct observation of potential distribution across Si/Sipâ€njunctions using offâ€axis electron holography. Applied Physics Letters, 1994, 65, 2603-2605.	1.5	129
31	Endotaxial Silicide Nanowires. Physical Review Letters, 2004, 93, 256102.	2.9	119
32	Chemical Vapor Deposition Synthesis of N-, P-, and Si-Doped Single-Walled Carbon Nanotubes. ACS Nano, 2010, 4, 1696-1702.	7.3	113
33	Coral bleaching patterns are the outcome of complex biological and environmental networking. Global Change Biology, 2020, 26, 68-79.	4.2	111
34	Direct observation of the surfaces of small metal crystallites: rhodium supported on titania. Langmuir, 1988, 4, 827-830.	1.6	109
35	Power-by-the-hour: the role of technology in reshaping business strategy at Rolls-Royce. Technology Analysis and Strategic Management, 2013, 25, 987-1007.	2.0	107
36	Structural properties of InN films grown on GaAs substrates: observation of the zincblende polytpe. Journal of Crystal Growth, 1993, 127, 204-208.	0.7	104

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37	Reversibility of strong metal-support interactions on Rh/TiO2. Journal of Catalysis, 1989, 118, 227-237.	3.1	103
38	Spin-dependent transport ofCoâˆ'SiO2granular films approaching percolation. Physical Review B, 2000, 62, 14273-14278.	1.1	100
39	Optical properties of GaN grown on ZnO by reactive molecular beam epitaxy. Applied Physics Letters, 1997, 70, 467-469.	1.5	99
40	Electron microscopy at 1-Ã... resolution by entropy maximization and likelihood ranking. Nature, 1992, 355, 605-609.	13.7	97
41	Microstructure and optical properties of epitaxial GaN on ZnO (0001) grown by reactive molecular beam epitaxy. Journal of Applied Physics, 1998, 83, 983-990.	1.1	97
42	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi₂Te₃ by Multifunctionality of Native Defects. Advanced Materials, 2015, 27, 3681-3686.	11.1	97
43	The realization of atomic resolution with the electron microscope. Reports on Progress in Physics, 1997, 60, 1513-1580.	8.1	95
44	Mapping of Electrostatic Potential in Deep Submicron CMOS Devices by Electron Holography. Physical Review Letters, 2002, 89, 025502.	2.9	95
45	Sperm motility: is viscosity fundamental to progress?. Molecular Human Reproduction, 2011, 17, 539-544.	1.3	95
46	Towards quantitative electron holography of magnetic thin films using in situ magnetization reversal. Ultramicroscopy, 1998, 74, 61-73.	0.8	93
47	Vapor-liquid-solid growth of germanium nanostructures on silicon. Journal of Applied Physics, 2004, 96, 7556-7567.	1.1	92
48	The electron-beam-induced reduction of transition metal oxide surfaces to metallic lower oxides. Ultramicroscopy, 1987, 23, 299-303.	0.8	91
49	High resolution studies of small particles of gold and silver. Journal of Crystal Growth, 1981, 54, 433-438.	0.7	90
50	Direct atomic imaging of solid surfaces. Ultramicroscopy, 1985, 16, 101-113.	0.8	90
51	Magnetic interactions within patterned cobalt nanostructures using off-axis electron holography. Journal of Applied Physics, 1998, 84, 374-378.	1.1	90
52	Rapid optofluidic detection of biomarkers for traumatic brain injury via surface-enhanced Raman spectroscopy. Nature Biomedical Engineering, 2020, 4, 610-623.	11.6	87
53	Chemical vapor deposition of heteroepitaxial Si1âˆ'xâˆ'yGexCy films on (100)Si substrates. Applied Physics Letters, 1994, 65, 2559-2561.	1.5	86
54	Characterization of structural defects in wurtzite GaN grown on 6H SiC using plasmaâ€enhanced molecular beam epitaxy. Applied Physics Letters, 1995, 67, 1830-1832.	1.5	86

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55	Finite size effects on the moment and ordering temperature in antiferromagnetic CoO layers. Physical Review B, 2003, 67, .	1.1	85
56	Left-Right Organizer Flow Dynamics: How Much Cilia Activity Reliably Yields Laterality?. Developmental Cell, 2014, 29, 716-728.	3.1	85
57	Interface structures in betaâ€silicon carbide thin films. Applied Physics Letters, 1987, 50, 203-205.	1.5	83
58	HREM and STEM of defects in multiplyâ€twinned particles. Journal of Microscopy, 1983, 130, 249-261.	0.8	82
59	Atomic-resolution study of structural rearrangements in small platinum crystals. Ultramicroscopy, 1986, 20, 71-75.	0.8	82
60	Epitaxial lateral overgrowth of (112Â¯2) semipolar GaN on (11Â¯00) m-plane sapphire by metalorganic chemical vapor deposition. Applied Physics Letters, 2007, 90, 182109.	1.5	82
61	Enhancing Exchange Bias with Diluted Antiferromagnets. Physical Review Letters, 2006, 96, 117204.	2.9	81
62	Coral microbiome diversity reflects mass coral bleaching susceptibility during the 2016 El NiÃ±o heat wave. Ecology and Evolution, 2019, 9, 938-956.	0.8	81
63	Nanometer-scale composition measurements of Ge/Si(100) islands. Applied Physics Letters, 2003, 82, 1473-1475.	1.5	77
64	An Atomistic Branching Mechanism for Carbon Nanotubes: Sulfur as the Triggering Agent. Angewandte Chemie - International Edition, 2008, 47, 2948-2953.	7.2	76
65	Formation of a Tetrameric, Cyclooctane-like, Azidochlorogallane, [HClGaN3]4, and Related Azidogallanes. Exothermic Single-Source Precursors to GaN Nanostructures. Journal of the American Chemical Society, 1998, 120, 5233-5237.	6.6	75
66	Carrier density modulation in a germanium heterostructure by ferroelectric switching. Nature Communications, 2015, 6, 6067.	5.8	75
67	Coral microbiome composition along the northern Red Sea suggests high plasticity of bacterial and specificity of endosymbiotic dinoflagellate communities. Microbiome, 2020, 8, 8.	4.9	75
68	Quantitative analysis of one-dimensional dopant profile by electron holography. Applied Physics Letters, 2002, 80, 3213-3215.	1.5	74
69	Characterization of Al(Cr)N and Ga(Cr)N dilute magnetic semiconductors. Journal of Magnetism and Magnetic Materials, 2005, 290-291, 1395-1397.	1.0	74
70	Magnetic iron silicide nanowires on Si(110). Applied Physics Letters, 2006, 88, 113111.	1.5	73
71	Formation of metastable phases in magnesiumâ€“titanium system by high-pressure torsion and their hydrogen storage performance. Acta Materialia, 2015, 99, 150-156.	3.8	73
72	Magnetic anisotropy and microstructure in molecular beam epitaxial FePt (110)/MgO (110). Journal of Applied Physics, 1998, 84, 934-939.	1.1	72

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73	Procedures for focusing, stigmating and alignment in high resolution electron microscopy. Journal of Microscopy, 1983, 130, 187-201.	0.8	70
74	The determination of atomic positions in high-resolution electron micrographs. Ultramicroscopy, 1985, 18, 39-47.	0.8	70
75	Magnetic correlations in non-percolated Coâ€“SiO2 granular films. Journal of Magnetism and Magnetic Materials, 2000, 221, 1-9.	1.0	70
76	Direct atomic imaging of solid surfaces. Surface Science, 1984, 143, 495-508.	0.8	69
77	High quality large-area CdTe(211)B on Si(211) grown by molecular beam epitaxy. Applied Physics Letters, 1997, 71, 1810-1812.	1.5	69
78	Prevention of Adrenal Crisis: Cortisol Responses to Major Stress Compared to Stress Dose Hydrocortisone Delivery. Journal of Clinical Endocrinology and Metabolism, 2020, 105, 2262-2274.	1.8	68
79	Correlation of coercivity and microstructure of thin CoFe films. Journal of Applied Physics, 2000, 88, 2058-2062.	1.1	67
80	Physics of rheologically enhanced propulsion: Different strokes in generalized Stokes. Physics of Fluids, 2013, 25, .	1.6	67
81	Direct Observation of Elastic and Plastic Deformations at Au(111) Surfaces. Physical Review Letters, 1984, 52, 656-658.	2.9	66
82	Atomic resolution electron microscopy of NiO grain boudaries. Ultramicroscopy, 1987, 22, 57-70.	0.8	66
83	Grain boundary structure in Alâ€“Mg and Alâ€“Mgâ€“Sc alloys after equal-channel angular pressing. Journal of Materials Research, 2001, 16, 583-589.	1.2	66
84	Observation of vertical honeycomb structure in InAlNâˆ•GaN heterostructures due to lateral phase separation. Applied Physics Letters, 2007, 90, 081917.	1.5	64
85	Plastic Deformation of BaTiO₃Ceramics by High-pressure Torsion and Changes in Phase Transformations, Optical and Dielectric Properties. Materials Research Letters, 2015, 3, 216-221.	4.1	64
86	Atomic-scale Chemical Imaging and Quantification of Metallic Alloy Structures by Energy-Dispersive X-ray Spectroscopy. Scientific Reports, 2014, 4, 3945.	1.6	64
87	Novel Synthetic Routes to Carbon Nitride. Chemistry of Materials, 1995, 7, 1422-1426.	3.2	61
88	Switching asymmetries in closely coupled magnetic nanostructure arrays. Applied Physics Letters, 1999, 75, 2641-2643.	1.5	61
89	Electron-beam-induced reactions at transition-metal oxide surfaces. Vacuum, 1991, 42, 301-308.	1.6	59
90	Growth and characterization of pseudomorphic single crystal zinc blende MnS. Applied Physics Letters, 1995, 67, 2690-2692.	1.5	59

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91	Talented suppliers? Strategic change and innovation in the UK aerospace industry. R and D Management, 2005, 35, 37-49.	3.0	58
92	Development of Aberration-Corrected Electron Microscopy. Microscopy and Microanalysis, 2008, 14, 2-15.	0.2	58
93	A homologous series of recurrent intergrowth structures of the type Bi4Am + n â^' 2Bm + nO3(m + n) + 6 formed by oxides of the aurivillius family. Journal of Solid State Chemistry, 1984, 55, 101-105.	1.4	57
94	Tunable band structure in diamondâ€“cubic tinâ€“germanium alloys grown on silicon substrates. Solid State Communications, 2003, 127, 355-359.	0.9	57
95	Methods for the measurement of rigid-body displacements at edge-on boundaries using high-resolution electron microscopy. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1985, 50, 375-391.	0.8	56
96	Characterization of Group III-nitride semiconductors by high-resolution electron microscopy. Journal of Crystal Growth, 1995, 152, 135-142.	0.7	56
97	Dynamic observation of defect annealing in CdTe at lattice resolution. Nature, 1982, 298, 127-131.	13.7	55
98	Dysprosium silicide nanowires on Si(110). Applied Physics Letters, 2003, 83, 5292-5294.	1.5	55
99	Effectiveness of TiN porous templates on the reduction of threading dislocations in GaN overgrowth by organometallic vapor-phase epitaxy. Applied Physics Letters, 2005, 86, 043108.	1.5	55
100	Microstructure of heteroepitaxial CdTe grown on misoriented Si(001) substrates. Applied Physics Letters, 1995, 67, 1591-1593.	1.5	54
101	Structural properties of GaN films grown on sapphire by molecular beam epitaxy. Applied Physics Letters, 1996, 68, 1141-1143.	1.5	54
102	Endotaxial silicide nanowires: A review. Thin Solid Films, 2011, 519, 8434-8440.	0.8	53
103	Origin of Magnetization Decay in Spin-Dependent Tunnel Junctions. Science, 1999, 286, 1337-1340.	6.0	52
104	Sub-250 nm room-temperature optical gain from AlGaN/AlN multiple quantum wells with strong band-structure potential fluctuations. Applied Physics Letters, 2012, 100, 061111.	1.5	52
105	The measurement of boundary displacements in metals. Ultramicroscopy, 1984, 14, 145-154.	0.8	51
106	Atomic imaging of oxide surfaces. Surface Science, 1986, 175, 673-683.	0.8	51
107	Measurement of lattice-fringe vectors from digital HREM images: experimental precision. Ultramicroscopy, 1995, 57, 409-422.	0.8	51
108	Fabrication and thermal stability of a nanocrystalline Niâ€“Alâ€“Cr alloy: Comparison with pure Cu and Ni. Journal of Materials Research, 1999, 14, 4200-4207.	1.2	51

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109	Efficient p-type doping of GaN films by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2004, 85, 4956-4958.	1.5	51
110	The Role of Sulfur in the Synthesis of Novel Carbon Morphologies: From Covalent Yâ€Junctions to Seaâ€Urchinâ€Like Structures. Advanced Functional Materials, 2009, 19, 1193-1199.	7.8	51
111	Atomic resolution with a 600-kV electron microscope. Nature, 1979, 281, 49-51.	13.7	49
112	Non-anomalous high-resolution imaging of crystalline materials. Ultramicroscopy, 1985, 16, 19-31.	0.8	49
113	Synthesis and characterization of heteroepitaxial diamondâ€structured Ge1â^'xCx (x=1.5â€“5.0%) alloys using chemical vapor deposition. Applied Physics Letters, 1996, 68, 2407-2409.	1.5	49
114	Off-axis electron holography of epitaxial FePt films. Journal of Applied Physics, 1997, 82, 2461-2465.	1.1	49
115	Mapping In concentration, strain, and internal electric field in InGaN/GaN quantum well structure. Applied Physics Letters, 2004, 84, 2103-2105.	1.5	49
116	Effect of microstructure on magnetic properties and anisotropy distributions in Co/Pd thin films and nanostructures. Physical Review B, 2009, 80, .	1.1	49
117	Î±-1-Antitrypsin variants and the proteinase/antiproteinase imbalance in chronic obstructive pulmonary disease. American Journal of Physiology - Lung Cellular and Molecular Physiology, 2015, 308, L179-L190.	1.3	49
118	Motile curved bacteria are Pareto-optimal. Proceedings of the National Academy of Sciences of the United States of America, 2019, 116, 14440-14447.	3.3	49
119	Optimisation and applications of the Cambridge University 600 kV high resolution electron microscope. Ultramicroscopy, 1982, 9, 203-213.	0.8	48
120	The high resolution electron microscopy of stacking defects in Cuâ€“Znâ€“Al shape memory alloy. Journal of Microscopy, 1983, 129, 295-306.	0.8	48
121	Magnetic tunnel junctions thermally stable to above 300â€ŠÂ°C. Applied Physics Letters, 1999, 75, 543-545.	1.5	48
122	Annealing of CoFeB/MgO based single and double barrier magnetic tunnel junctions: Tunnel magnetoresistance, bias dependence, and output voltage. Journal of Applied Physics, 2009, 105, .	1.1	48
123	Reliability studies of AlGaN/GaN high electron mobility transistors. Semiconductor Science and Technology, 2013, 28, 074019.	1.0	48
124	Direct observation of the structure of a metallic alloy glass. Nature, 1979, 281, 465-467.	13.7	47
125	Observations of nanocrystals in thin TbFeCo films. Applied Physics Letters, 1989, 55, 919-921.	1.5	47
126	Studies of electron irradiation and annealing effects on TiO2 surfaces in ultrahigh vacuum using high-resolution electron microscopy. Surface Science, 1991, 250, 169-178.	0.8	47

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127	Dependence of giant magnetoresistance on Cu-layer thickness in Co/Cu multilayers: A simple dilution effect. Physical Review B, 1993, 47, 9136-9139.	1.1	47
128	Simple chemical routes to diamond-cubic germaniumâ€“tin alloys. Applied Physics Letters, 2001, 78, 3607-3609.	1.5	47
129	Impact of severe plastic deformation on microstructure and hydrogen storage of titanium-iron-manganese intermetallics. Scripta Materialia, 2016, 124, 108-111.	2.6	47
130	Epitaxial titanium silicide islands and nanowires. Surface Science, 2003, 524, 148-156.	0.8	46
131	Observation of Hole Accumulation in Ge/Si Core/Shell Nanowires Using off-Axis Electron Holography. Nano Letters, 2011, 11, 493-497.	4.5	46
132	Interaction of small and extended defects in nonstoichiometric oxides. Nature, 1984, 309, 319-321.	13.7	45
133	Electron microscopy study of Ni/Ni3Al diffusion-couple interfaceâ€”I. Microstructural observation and microchemical analysis. Acta Metallurgica Et Materialia, 1994, 42, 3381-3387.	1.9	45
134	Quantitative phase imaging of nanoscale electrostatic and magnetic fields using off-axis electron holography. Ultramicroscopy, 2010, 110, 375-382.	0.8	45
135	Atomic and electronic structure of the ferroelectric BaTiO3/Ge(001) interface. Applied Physics Letters, 2014, 104, .	1.5	45
136	Evaluation of antimony segregation in InAs/InAs1â^'xSbx type-II superlattices grown by molecular beam epitaxy. Journal of Applied Physics, 2016, 119, .	1.1	45
137	Oriented Growth of Single-Crystal Ni Nanowires onto Amorphous SiO₂. Nano Letters, 2010, 10, 5070-5075.	4.5	44
138	Epitaxial strontium titanate films grown by atomic layer deposition on SrTiO3-buffered Si(001) substrates. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	0.9	44
139	Low-threshold continuous-wave operation of quantum-cascade lasers grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2004, 85, 5842-5844.	1.5	43
140	Defect characterization for epitaxial HgCdTe alloys by electron microscopy. Journal of Crystal Growth, 2004, 265, 224-234.	0.7	43
141	Atomic layer deposition of crystalline SrHfO3 directly on Ge (001) for high-k dielectric applications. Journal of Applied Physics, 2015, 117, .	1.1	43
142	Applications of electron holography to the study of interfaces. Ultramicroscopy, 1993, 50, 301-311.	0.8	42
143	SnGe superstructure materials for Si-based infrared optoelectronics. Applied Physics Letters, 2003, 83, 3489-3491.	1.5	42
144	Reverse Leakage Analysis for As-Grown and Regrown Vertical GaN-on-GaN Schottky Barrier Diodes. IEEE Journal of the Electron Devices Society, 2020, 8, 74-83.	1.2	42

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145	Atom hopping on small gold particles imaged by high-resolution electron microscopy. Die Naturwissenschaften, 1985, 72, 539-541.	0.6	41
146	A Joint Structural Characterization of Colloidal Platinum by EXAFS and High-Resolution Electron Microscopy. Angewandte Chemie International Edition in English, 1989, 28, 590-593.	4.4	41
147	Spin-dependent tunneling in discontinuous Coâ€“SiO2 magnetic tunnel junctions. Applied Physics Letters, 1998, 73, 535-537.	1.5	41
148	Influence of interface alloying on the magnetic properties of Co/Pd multilayers. Applied Physics Letters, 2003, 83, 5259-5261.	1.5	41
149	Hollow metallic microspheres produced by spark erosion. Applied Physics Letters, 2004, 85, 940-942.	1.5	41
150	The role of Cr substitution on the ferromagnetic properties of Ga1â^'xCrxN. Applied Physics Letters, 2005, 86, 012504.	1.5	41
151	Modelling the fluid mechanics of cilia and flagella in reproduction and development. European Physical Journal E, 2012, 35, 111.	0.7	41
152	Real-Time Atomic-Resolution Imaging of Polymorphic Changes in Ruthenium Clusters. Angewandte Chemie International Edition in English, 1988, 27, 555-558.	4.4	40
153	Growth and characterization of CdTe/Si heterostructures â€" effect of substrate orientation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 77, 93-100.	1.7	40
154	Decorating carbon nanotubes with nanostructured nickel particles via chemical methods. Chemical Physics Letters, 2006, 431, 104-109.	1.2	40
155	Quenched magnetic moment in Mn-doped amorphous Si films. Physical Review B, 2008, 77, .	1.1	40
156	A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors. Advanced Materials Interfaces, 2014, 1, 1400081.	1.9	40
157	Large positive linear magnetoresistance in the two-dimensional t 2g electron gas at the EuO/SrTiO3 interface. Scientific Reports, 2018, 8, 7721.	1.6	40
158	Direct lattice imaging of small metal particles. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1981, 44, 735-740.	0.8	39
159	â€œMetallisationâ€•of oxide surfaces observed by in situ high-resolution electron microscopy. Ultramicroscopy, 1985, 17, 387-391.	0.8	39
160	The oxidation of small rhodium metal particles. Ultramicroscopy, 1989, 31, 132-137.	0.8	38
161	Novel chemical routes to siliconâ€germaniumâ€carbon materials. Applied Physics Letters, 1994, 65, 2960-2962.	1.5	38
162	Influence of 6Hâ€“SiC(0001) substrate surface morphology on the growth of AlN epitaxial layers. Applied Physics Letters, 1999, 74, 985-987.	1.5	38

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163	Molecular beam epitaxy of InAlNâˆ•GaN heterostructures for high electron mobility transistors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1204.	1.6	38
164	Complex and incommensurate ordering in Al0.72Ga0.28N thin films grown by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2006, 88, 181915.	1.5	38
165	Electric-Field-Driven Degradation in off-State Step-Stressed AlGaN/GaN High-Electron Mobility Transistors. IEEE Transactions on Device and Materials Reliability, 2011, 11, 187-193.	1.5	38
166	Observations of silicon carbide by high resolution transmission electron microscopy. Journal of Microscopy, 1978, 114, 1-18.	0.8	37
167	A systematic analysis of HREM imaging of sphalerite semiconductors. Ultramicroscopy, 1989, 27, 131-150.	0.8	37
168	Epitaxial relationships in electron-stimulated desorption processes at transition metal oxide surfaces. Surface Science, 1989, 221, 214-232.	0.8	37
169	Development of a low-temperature GaN chemical vapor deposition process based on a single molecular source H2GaN3. Applied Physics Letters, 1999, 74, 883-885.	1.5	37
170	Intersubband absorption in AlNâˆ•GaNâˆ•AlGaN coupled quantum wells. Applied Physics Letters, 2007, 91, 141104.	1.5	37
171	Quasi-two-dimensional electron gas at the epitaxial alumina/SrTiO3 interface: Control of oxygen vacancies. Journal of Applied Physics, 2015, 117, .	1.1	37
172	Unraveling Hydrophobic Interactions at the Molecular Scale Using Force Spectroscopy and Molecular Dynamics Simulations. ACS Nano, 2017, 11, 2586-2597.	7.3	37
173	Determination of mean inner potential of germanium using off-axis electron holography. Acta Crystallographica Section A: Foundations and Advances, 1999, 55, 652-658.	0.3	36
174	Structure and orientation of epitaxial titanium silicide nanowires determined by electron microdiffraction. Journal of Applied Physics, 2003, 93, 5670-5674.	1.1	36
175	Defects at the surface of Î²-Ga2O3 produced by Ar plasma exposure. APL Materials, 2019, 7, .	2.2	36
176	A theoretical analysis of HREM imaging for â€˜110â€™ tetrahedral semiconductors. Ultramicroscopy, 1989, 27, 19-34.	0.8	35
177	Dependence of giant magnetoresistance on grain size in Co/Cu multilayers. Physical Review B, 1994, 50, 4232-4235.	1.1	35
178	Long wavelength (1.3 and 1.5 Î¼m) photoluminescence from InGaAs/GaPAsSb quantum wells grown on GaAs. Applied Physics Letters, 1999, 75, 1267-1269.	1.5	35
179	Defect annihilation in AlN thin films by ultrahigh temperature processing. Applied Physics Letters, 2000, 76, 1839-1841.	1.5	35
180	Semiconductor dopant profiling by off-axis electron holography. Ultramicroscopy, 2003, 94, 149-161.	0.8	35

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181	Nanosynthesis Routes to New Tetrahedral Crystalline Solids: Silicon-like Si₃AlP. Journal of the American Chemical Society, 2011, 133, 16212-16218.	6.6	35
182	Characterization of Bi2Te3 and Bi2Se3 topological insulators grown by MBE on (001) GaAs substrates. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	0.6	35
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